

NTMFS4833NS

Power MOSFET

30 V, 156 A, Single N-Channel, SO-8 FL

Features

- Accurate, Lossless Current Sensing
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Value | Unit | |
|--|----------------|--------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 30 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JA}$ (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 26 | A |
| | | $T_A = 85^\circ\text{C}$ | 18 | |
| Power Dissipation $R_{\theta JA}$ (Note 1) | P_D | $T_A = 25^\circ\text{C}$ | 2.31 | W |
| | | | | |
| Continuous Drain Current $R_{\theta JA}$ (Note 2) | I_D | $T_A = 25^\circ\text{C}$ | 16 | A |
| | | $T_A = 85^\circ\text{C}$ | 11.6 | |
| Power Dissipation $R_{\theta JA}$ (Note 2) | P_D | $T_A = 25^\circ\text{C}$ | 0.9 | W |
| | | | | |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | I_D | $T_C = 25^\circ\text{C}$ | 156 | A |
| | | $T_C = 85^\circ\text{C}$ | 113 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | P_D | $T_C = 25^\circ\text{C}$ | 86.2 | W |
| | | | | |
| Pulsed Drain Current | I_{DM} | 312 | A | |
| $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | | | | |
| Operating Junction and Storage Temperature | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 86 | A | |
| Drain to Source DV/DT | dV/dt | 6 | V/ns | |
| Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, V_{DD} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_L = 35 \text{ A}_{pk}, L = 1.0 \text{ mH}, R_G = 25 \Omega$) | EAS | 612.5 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

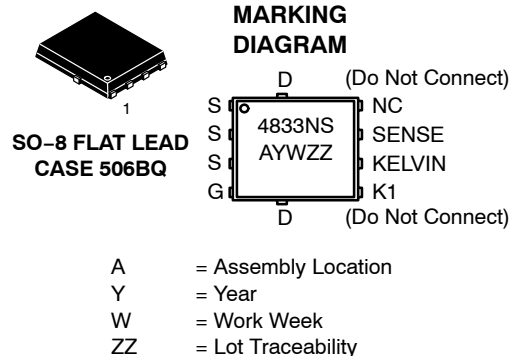
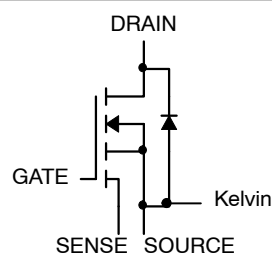
1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.



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| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 30 V | 2.2 m Ω @ 10 V | 156 A |
| | 3.4 m Ω @ 4.5 V | 127 A |



ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------|-------------------|------------------|
| NTMFS4833NST1G | SO-8 FL (Pb-Free) | 1500 Tape / Reel |
| NTMFS4833NST3G | SO-8 FL (Pb-Free) | 5000 Tape / Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|------|
| Junction-to-Case (Drain) | $R_{\theta JC}$ | 1.45 | °C/W |
| Junction-to-Ambient – Steady State (Note 3) | $R_{\theta JA}$ | 54 | |
| Junction-to-Ambient – Steady State (Note 4) | $R_{\theta JA}$ | 138.7 | |

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|-------------------|---|-----|-----|---------------------------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | 30 | | mV/°C |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$ | | | 1 | μA |
| | | | | | $T_J = 125^\circ\text{C}$ | |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |

ON CHARACTERISTICS (Note 5)

| | | | | | | | |
|--|------------------|---|---------------------|-----|-----|-------|------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$ | 1.5 | | 2.5 | V | |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 6.8 | | mV/°C | |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 30\text{ A}$ | | 1.4 | 2.2 | m Ω |
| | | | $I_D = 15\text{ A}$ | | 1.3 | | |
| | | $V_{GS} = 4.5\text{ V}$ | $I_D = 30\text{ A}$ | | 2.3 | 3.4 | |
| | | | $I_D = 15\text{ A}$ | | 2.3 | | |
| Forward Transconductance | g_{FS} | $V_{DS} = 15\text{ V}, I_D = 15\text{ A}$ | | 100 | | S | |

CHARGES, CAPACITANCES & GATE RESISTANCE

| | | | | | | |
|------------------------------|--------------|---|--|------|----|----|
| Input Capacitance | C_{ISS} | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 12\text{ V}$ | | 5250 | | pF |
| Output Capacitance | C_{OSS} | | | 1080 | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 500 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$ | | 36 | 63 | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 3.8 | | |
| Gate-to-Source Charge | Q_{GS} | | | 15 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 13 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$ | | 86 | | nC |

SWITCHING CHARACTERISTICS (Note 6)

| | | | | | | |
|---------------------|--------------|---|--|----|--|----|
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$ | | 21 | | ns |
| Rise Time | t_r | | | 60 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 37 | | |
| Fall Time | t_f | | | 44 | | |

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

7. With 0V potential from sense lead to source lead, i.e. using a virtual ground.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|--------------|---|-----|-----|-----|------|
| SWITCHING CHARACTERISTICS (Note 6) | | | | | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$ | | 11 | | ns |
| Rise Time | t_r | | | 34 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 53 | | |
| Fall Time | t_f | | | 34 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|----------|---|---------------------------|--|------|-----|----|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.80 | 1.2 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.67 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$ | | | 36 | | ns |
| Charge Time | t_a | | | | 18 | | |
| Discharge Time | t_b | | | | 18 | | |
| Reverse Recovery Charge | Q_{RR} | | | | | 32 | |

PACKAGE PARASITIC VALUES

| | | | | | | |
|-------------------|-------|--------------------------|--|-------|--|----------|
| Source Inductance | L_S | $T_A = 25^\circ\text{C}$ | | 0.65 | | nH |
| Drain Inductance | L_D | | | 0.005 | | nH |
| Gate Inductance | L_G | | | 1.84 | | nH |
| Gate Resistance | R_G | | | 1.4 | | Ω |

CURRENT SENSE CHARACTERISTICS

| | | | | | | |
|---|-------------|--|-----|-------|-----|---------------------|
| Current Sensing Ratio | I_{ratio} | $V_{GS} = 5\text{ V}, 0\text{-}70^\circ\text{C}, 5\text{-}20\text{ A}$ | 357 | 387 | 417 | |
| Current Sensing Ratio | I_{ratio} | $V_{GS} = 5\text{ V}, 0\text{-}70^\circ\text{C}, 1\text{-}5\text{ A}$ | 351 | 387 | 423 | |
| Current Sense Temperature Coefficient (Note 7) | | | | 0.006 | | %/ $^\circ\text{C}$ |
| Mirror Resistance | $r_{m(on)}$ | $V_{GS} = 5\text{ V}$ | | 0.80 | | Ω |

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.
- With 0V potential from sense lead to source lead, i.e. using a virtual ground.

TYPICAL CHARACTERISTIC CURVES

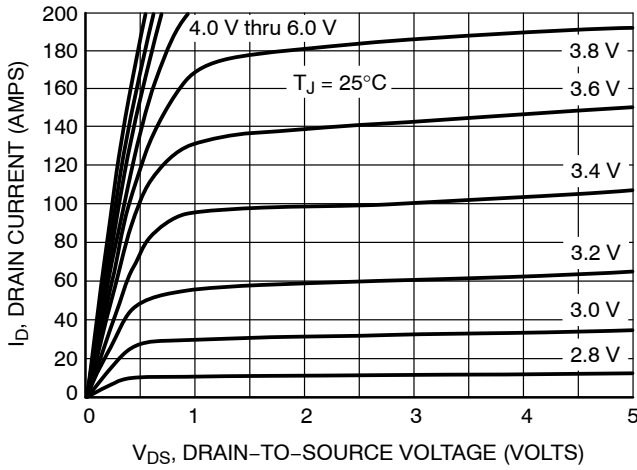


Figure 1. On-Region Characteristics

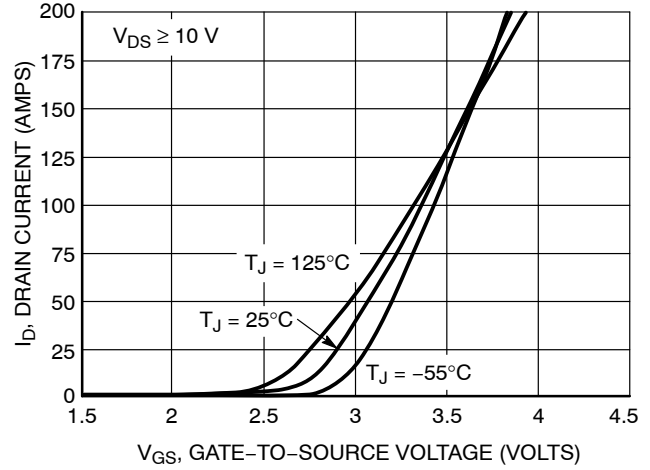


Figure 2. Transfer Characteristics

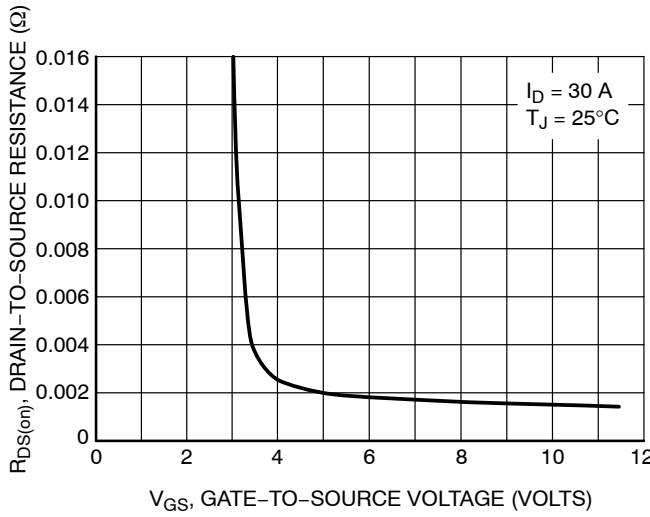


Figure 3. On-Resistance vs. Gate-to-Source Voltage

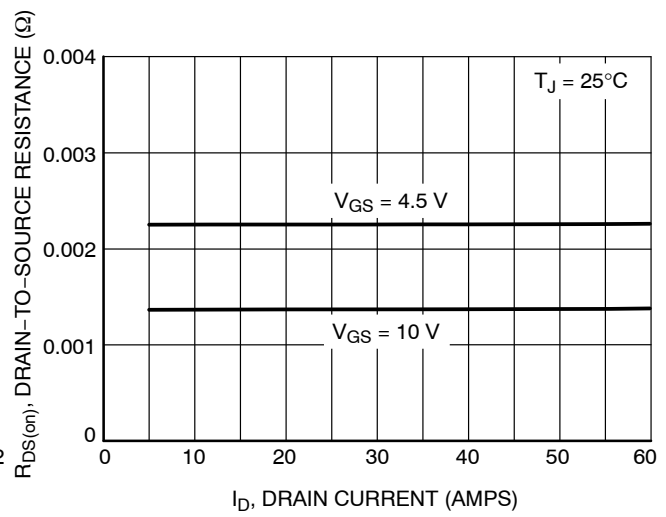


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

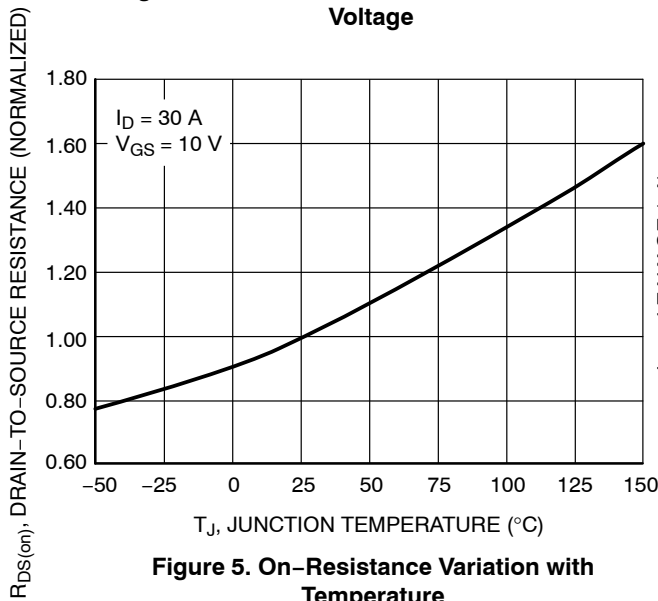


Figure 5. On-Resistance Variation with Temperature

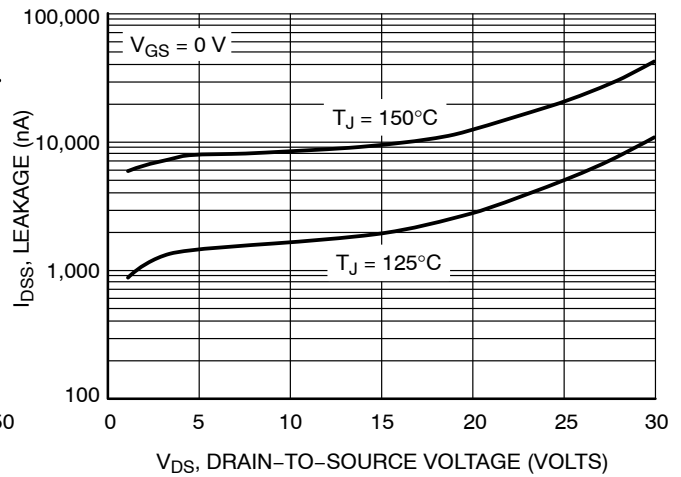


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTIC CURVES

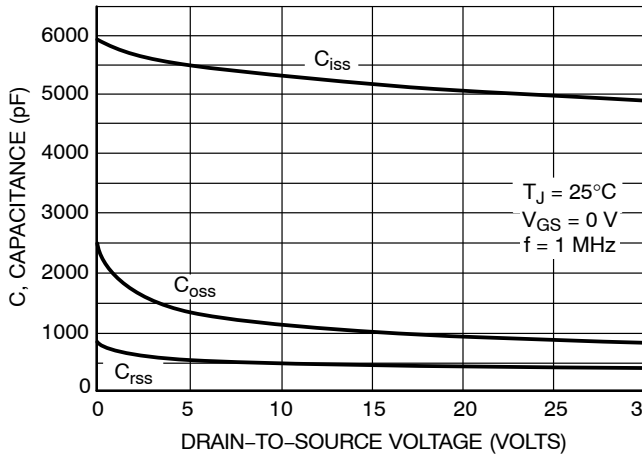


Figure 7. Capacitance Variation

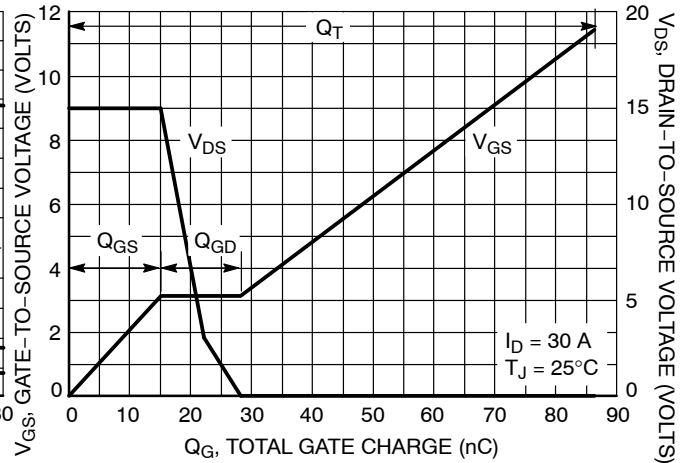


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

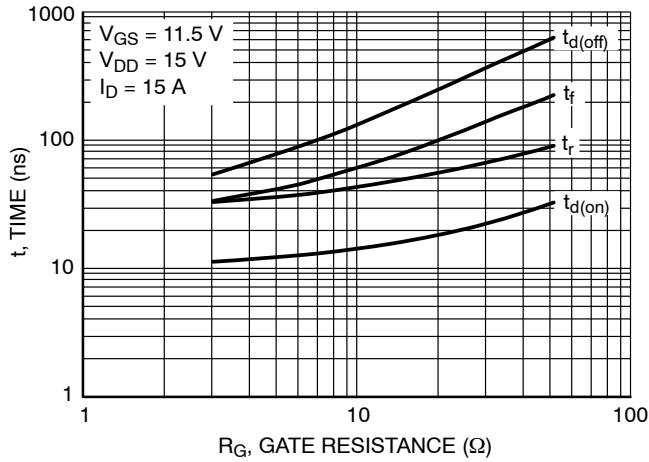


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

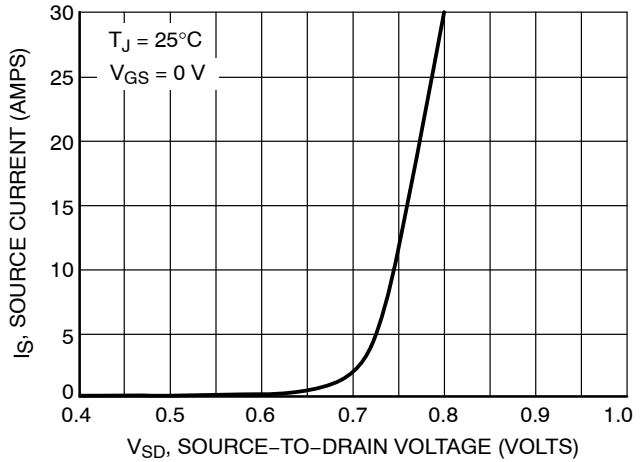


Figure 10. Diode Forward Voltage vs. Current

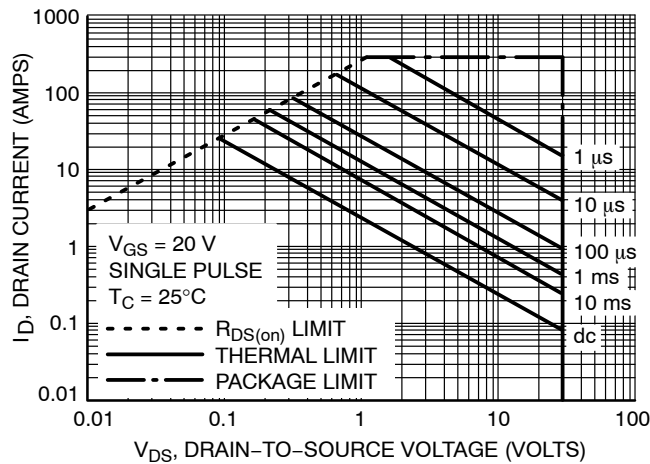


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

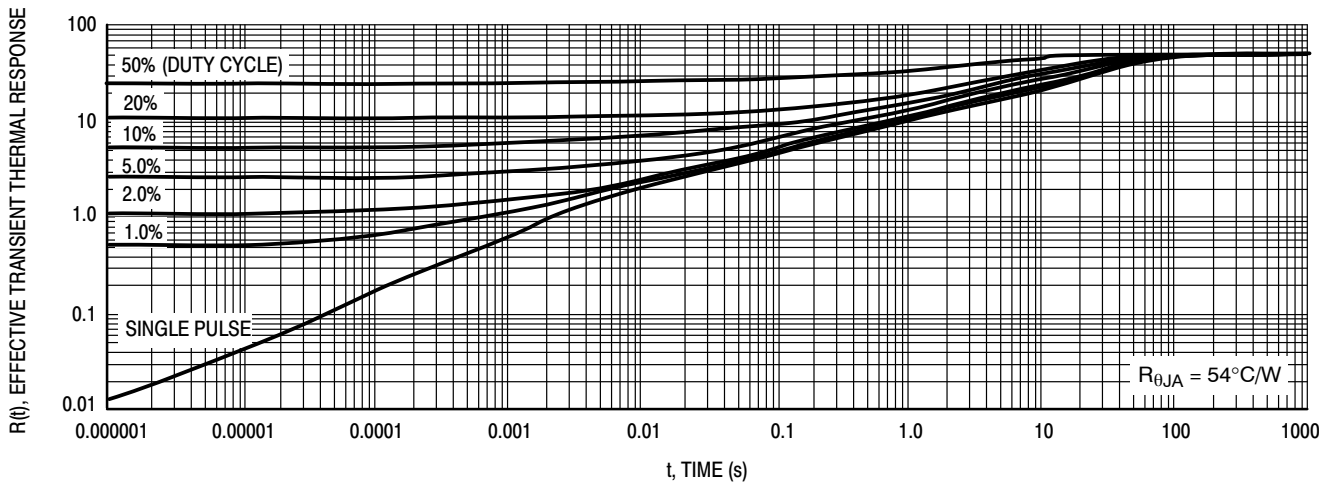
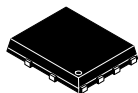


Figure 12. FET Thermal Response

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

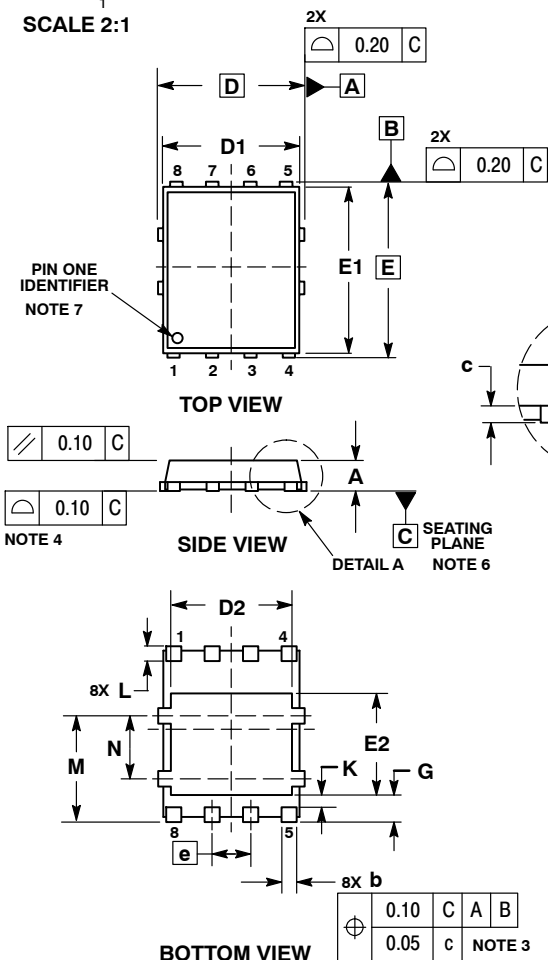
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1
SCALE 2:1

DFN8 5x6, 1.27P CASE 506BQ ISSUE C

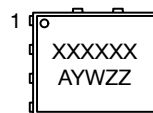
DATE 12 APR 2012



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINAL.
5. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

GENERIC MARKING DIAGRAM*

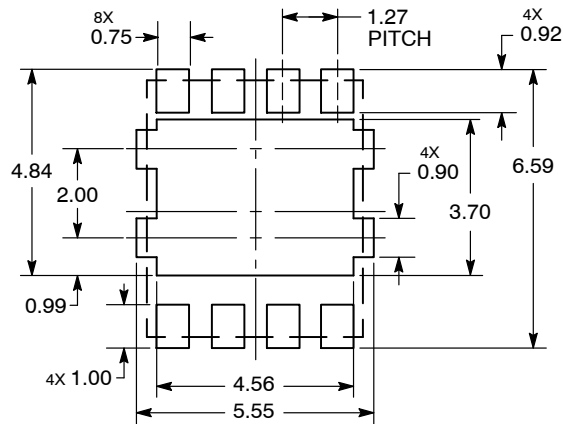


XXXXXX= Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

| DIM | MILLIMETERS | |
|-----|-------------|------|
| | MIN | MAX |
| A | 0.90 | 1.10 |
| A1 | --- | 0.05 |
| b | 0.33 | 0.51 |
| c | 0.20 | 0.33 |
| D | 5.15 BSC | |
| D1 | 4.50 | 5.10 |
| D2 | 3.90 | 4.30 |
| E | 6.15 BSC | |
| E1 | 5.50 | 6.10 |
| E2 | 3.00 | 3.50 |
| e | 1.27 BSC | |
| G | 0.80 | 1.20 |
| h | --- | 12 ° |
| K | 0.20 | --- |
| L | 0.51 | 0.71 |
| M | 3.25 | 3.75 |
| N | 1.80 | 2.20 |

*This information is generic. Please refer to device data sheet for actual part marking.

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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